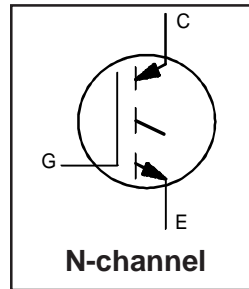


# IRG4IBC30SPbF

INSULATED GATE BIPOLAR TRANSISTOR

## Features

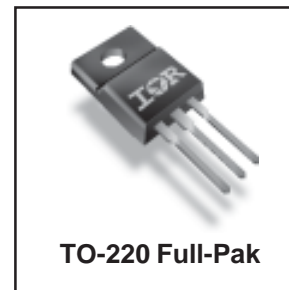
- Standard: Optimized for minimum saturation voltage and low operating frequencies (<1 kHz)
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than previous generation
- Industry standard TO-220 Full-Pak
- Lead-Free



|                                  |
|----------------------------------|
| $V_{CES} = 600V$                 |
| $V_{CE(on) \text{ typ.}} = 1.4V$ |
| @ $V_{GE} = 15V, I_C = 18A$      |

## Benefits

- Generation 4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- Designed to be a "drop-in" replacement for equivalent industry -standard Generation 3 IR IGBTs



## Absolute Maximum Ratings

|                           | Parameter  | Max.                              | Units      |
|---------------------------|--|-----------------------------------|------------|
| $V_{CES}$                 | Collector-to-Emitter Breakdown Voltage           | 600                               | V          |
| $I_C @ T_C = 25^\circ C$  | Continuous Collector Current                     | 23.5                              | A          |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current                     | 13.0                              |            |
| $I_{CM}$                  | Pulsed Collector Current ①                       | 68                                |            |
| $I_{LM}$                  | Clamped Inductive Load Current ②                 | 68                                |            |
| $V_{GE}$                  | Gate-to-Emitter Voltage                          | $\pm 20$                          | V          |
| $E_{ARV}$                 | Reverse Voltage Avalanche Energy ③               | 10                                | mJ         |
| $P_D @ T_C = 25^\circ C$  | Maximum Power Dissipation                        | 45                                | W          |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation                        | 18                                |            |
| $T_J$<br>$T_{STG}$        | Operating Junction and Storage Temperature Range | -55 to + 150                      | $^\circ C$ |
|                           | Soldering Temperature, for 10 seconds            | 300 (0.063 in. (1.6mm) from case) |            |

## Thermal Resistance

|                 | Parameter                                 | Typ.        | Max. | Units        |
|-----------------|---|-------------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case                          | —           | 2.8  | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | —           | 65   |              |
| Wt              | Weight                                    | 2.1 (0.075) | —    | g (oz)       |

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

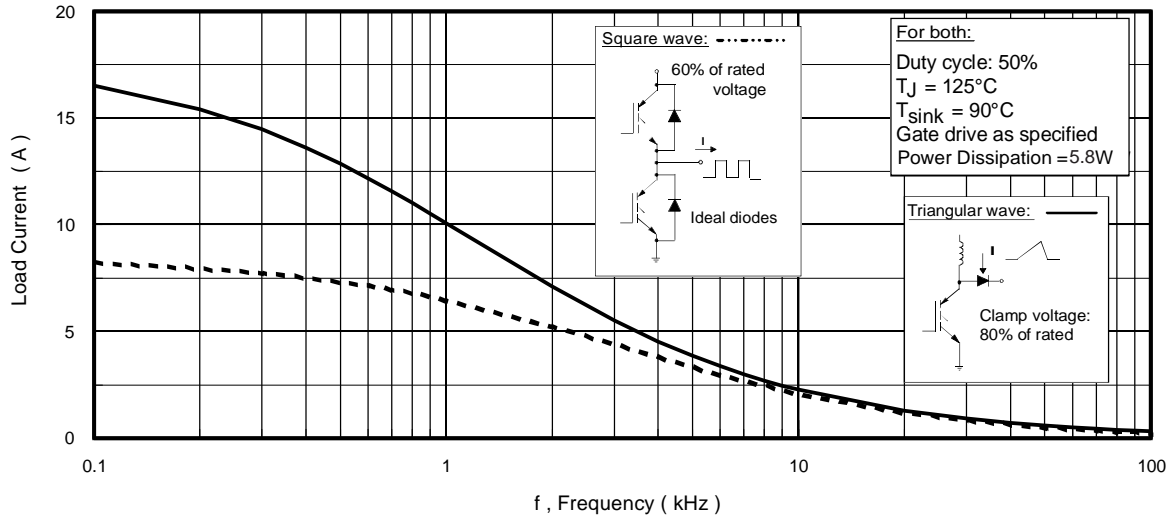
|                                 | Parameter                                | Min. | Typ. | Max.      | Units   | Conditions   |
|---------------------------------|--|------|------|-----------|---------|--|
| $V_{(BR)CES}$                   | Collector-to-Emitter Breakdown Voltage   | 600  | —    | —         | V       | $V_{GE} = 0V, I_C = 250\mu A$  |
| $V_{(BR)ECS}$                   | Emitter-to-Collector Breakdown Voltage ④ | 18   | —    | —         | V       | $V_{GE} = 0V, I_C = 1.0A$  |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage  | —    | 0.75 | —         | V/°C    | $V_{GE} = 0V, I_C = 1.0mA$   |
| $V_{CE(ON)}$                    | Collector-to-Emitter Saturation Voltage  | —    | 1.40 | 1.6       | V       | $I_C = 18A$<br>$I_C = 34A$<br>$I_C = 18A, T_J = 150^\circ\text{C}$<br>$V_{GE} = 15V$<br>See Fig.2, 5 |
|                                 |  | —    | 1.84 | —         |         |  |
|                                 |  | —    | 1.45 | —         |         |  |
| $V_{GE(th)}$                    | Gate Threshold Voltage                   | 3.0  | —    | 6.0       |         | $V_{CE} = V_{GE}, I_C = 250\mu A$  |
| $\Delta V_{GE(th)}/\Delta T_J$  | Temperature Coeff. of Threshold Voltage  | —    | -11  | —         | mV/°C   | $V_{CE} = V_{GE}, I_C = 250\mu A$  |
| $g_{fe}$                        | Forward Transconductance ⑤               | 6.0  | 11   | —         | S       | $V_{CE} = 100V, I_C = 18A$   |
| $I_{CES}$                       | Zero Gate Voltage Collector Current      | —    | —    | 250       | $\mu A$ | $V_{GE} = 0V, V_{CE} = 600V$   |
|                                 |  | —    | —    | 2.0       |         | $V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$  |
|                                 |  | —    | —    | 1000      |         | $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$  |
| $I_{GES}$                       | Gate-to-Emitter Leakage Current          | —    | —    | $\pm 100$ | nA      | $V_{GE} = \pm 20V$   |

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

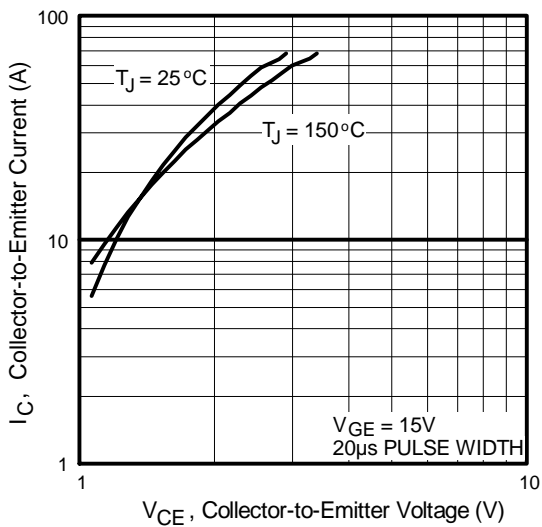
|              | Parameter                         | Min. | Typ. | Max. | Units | Conditions  |
|--------------|-----------------------------------|------|------|------|-------|---|
| $Q_g$        | Total Gate Charge (turn-on)       | —    | 50   | 75   | nC    | $I_C = 18A$<br>$V_{CC} = 400V$<br>$V_{GE} = 15V$<br>See Fig.8   |
| $Q_{ge}$     | Gate - Emitter Charge (turn-on)   | —    | 7.3  | 11   |       |   |
| $Q_{gc}$     | Gate - Collector Charge (turn-on) | —    | 17   | 26   |       |   |
| $t_{d(on)}$  | Turn-On Delay Time                | —    | 22   | —    | ns    | $T_J = 25^\circ\text{C}$<br>$I_C = 18A, V_{CC} = 480V$<br>$V_{GE} = 15V, R_G = 23\Omega$<br>Energy losses include "tail"<br>See Fig. 9, 10, 14    |
| $t_r$        | Rise Time                         | —    | 18   | —    |       |   |
| $t_{d(off)}$ | Turn-Off Delay Time               | —    | 540  | 810  |       |   |
| $t_f$        | Fall Time                         | —    | 390  | 590  |       |   |
| $E_{on}$     | Turn-On Switching Loss            | —    | 0.26 | —    | mJ    | See Fig. 9, 10, 14  |
| $E_{off}$    | Turn-Off Switching Loss           | —    | 3.45 | —    |       |   |
| $E_{ts}$     | Total Switching Loss              | —    | 3.71 | 5.6  |       |   |
| $t_{d(on)}$  | Turn-On Delay Time                | —    | 21   | —    | ns    | $T_J = 150^\circ\text{C},$<br>$I_C = 18A, V_{CC} = 480V$<br>$V_{GE} = 15V, R_G = 23\Omega$<br>Energy losses include "tail"<br>See Fig. 10, 11, 14 |
| $t_r$        | Rise Time                         | —    | 19   | —    |       |   |
| $t_{d(off)}$ | Turn-Off Delay Time               | —    | 790  | —    |       |   |
| $t_f$        | Fall Time                         | —    | 760  | —    |       |   |
| $E_{ts}$     | Total Switching Loss              | —    | 6.55 | —    | mJ    |   |
| $L_E$        | Internal Emitter Inductance       | —    | 7.5  | —    | nH    | Measured 5mm from package   |
| $C_{ies}$    | Input Capacitance                 | —    | 1100 | —    | pF    | $V_{GE} = 0V$<br>$V_{CC} = 30V$<br>$f = 1.0MHz$<br>See Fig. 7   |
| $C_{oes}$    | Output Capacitance                | —    | 72   | —    |       |   |
| $C_{res}$    | Reverse Transfer Capacitance      | —    | 19   | —    |       |   |

### Notes:

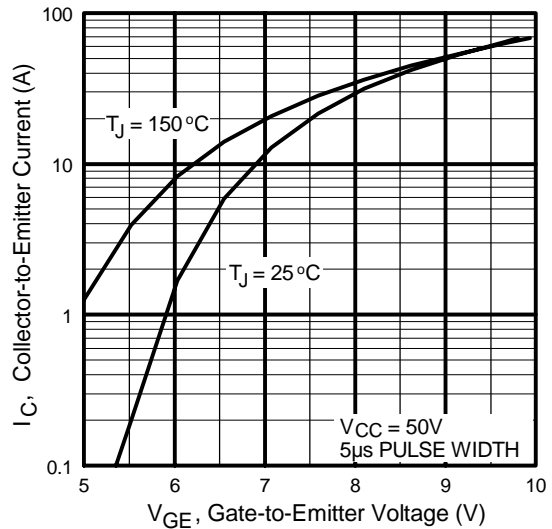
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. (See Fig. 13b)
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 23\Omega$ , (See Fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.



**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{RMS}$  of fundamental)



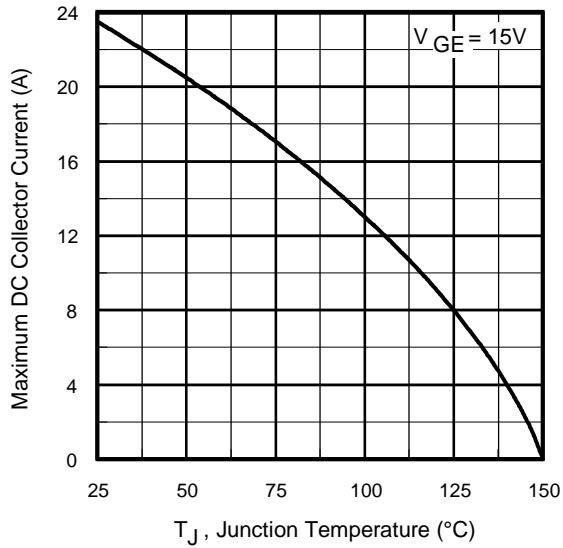
**Fig. 2 - Typical Output Characteristics**



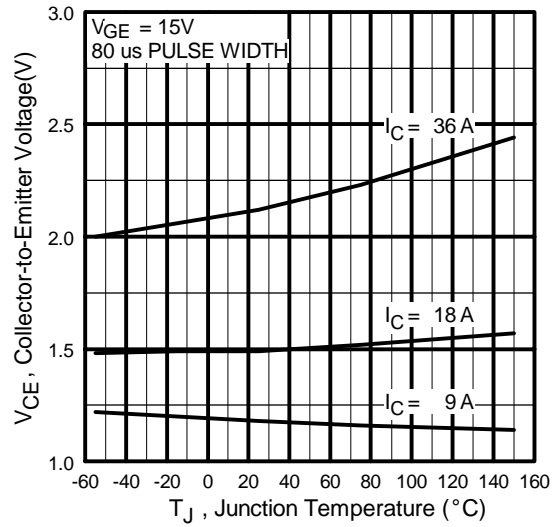
**Fig. 3 - Typical Transfer Characteristics**

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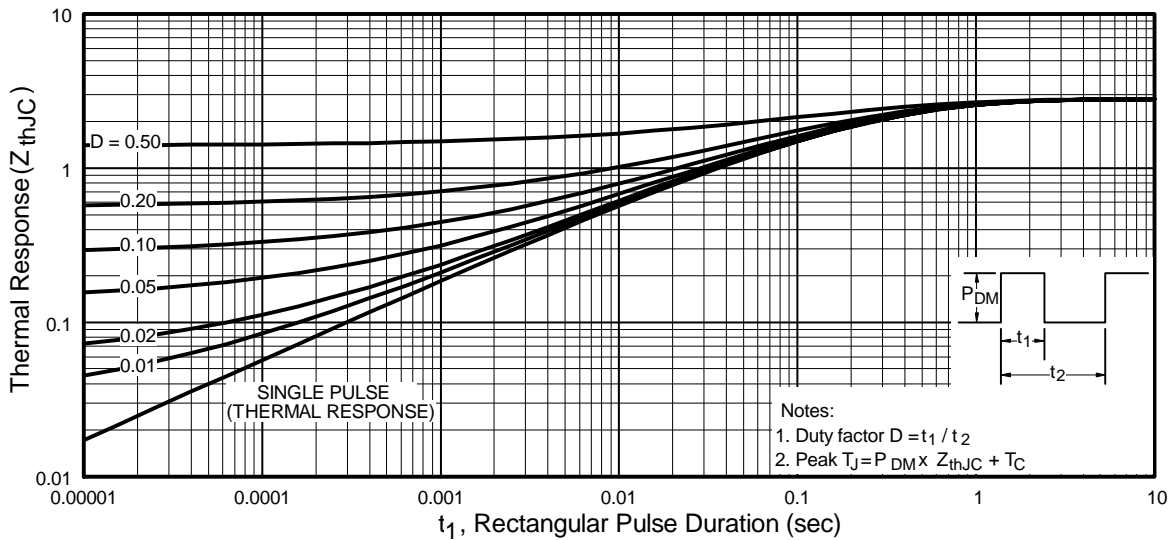
International  
**IRF** Rectifier



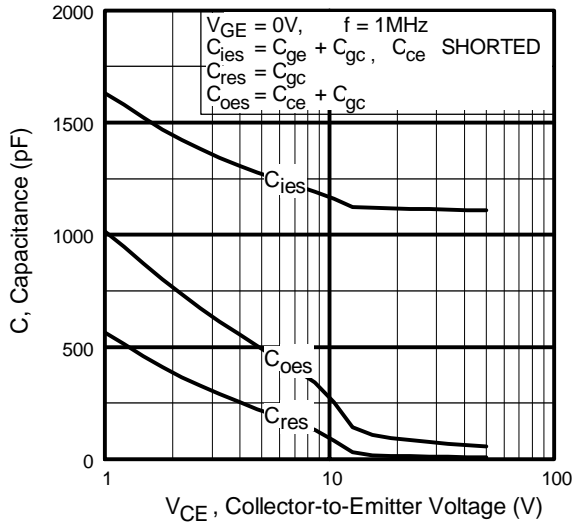
**Fig. 4** - Maximum Collector Current vs. Case Temperature



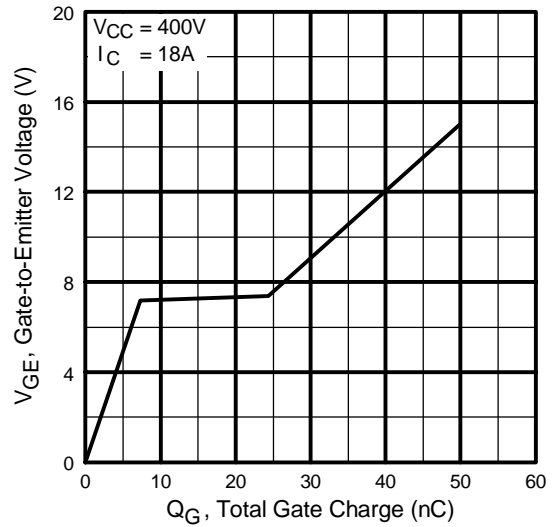
**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



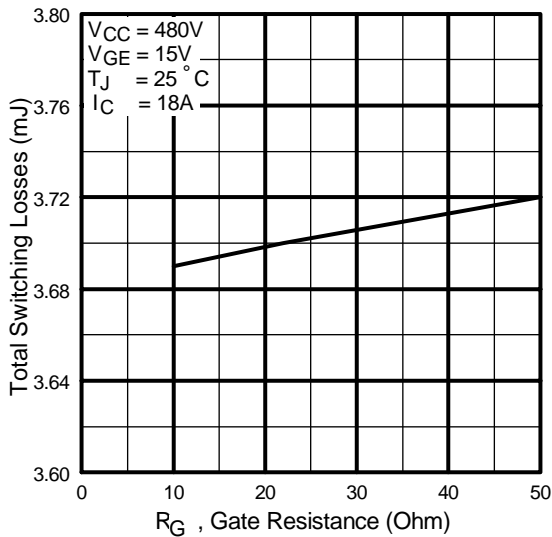
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case



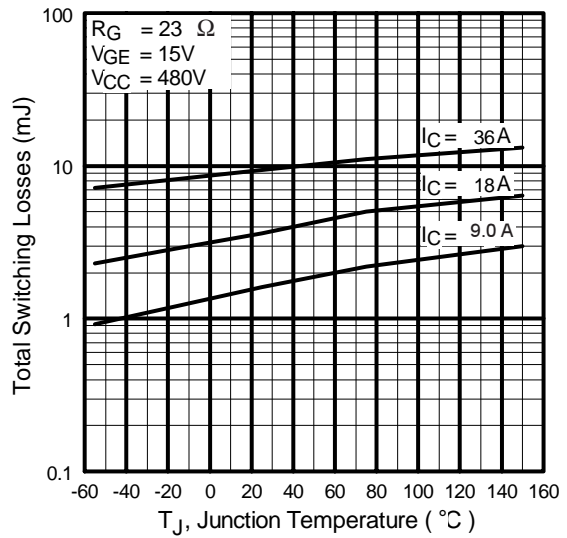
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

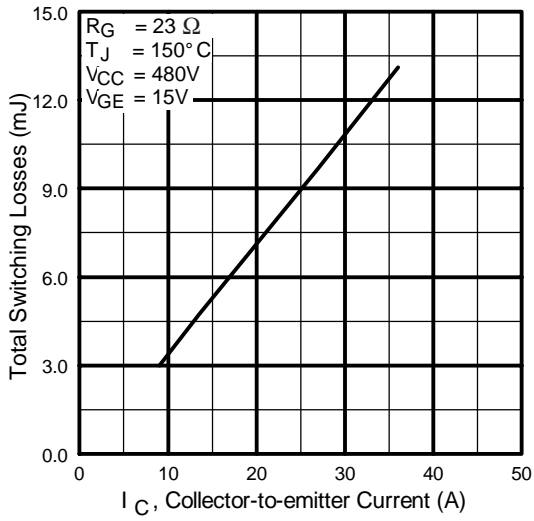


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

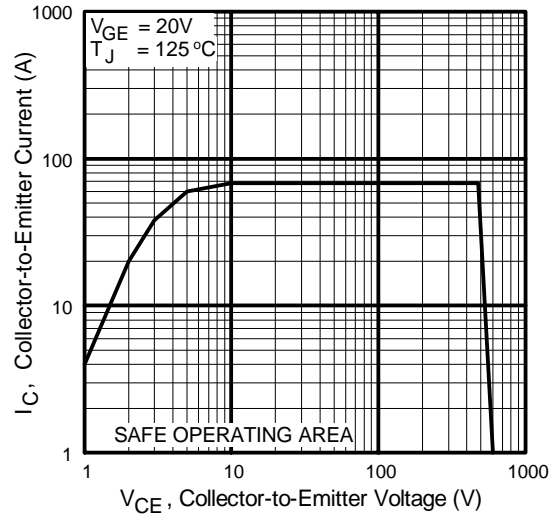


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

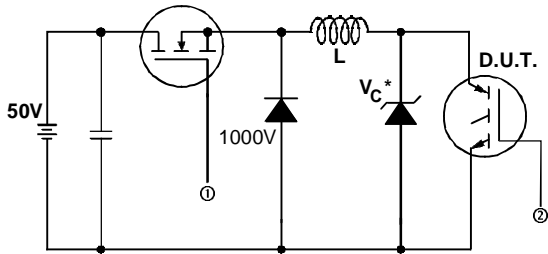
# IRG4IBC30SPbF



**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current

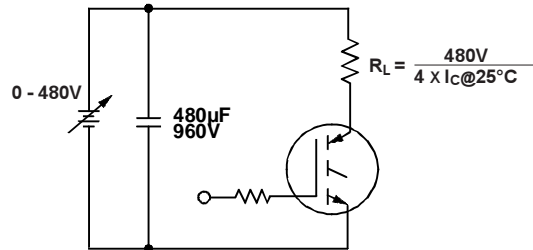


**Fig. 12** - Turn-Off SOA

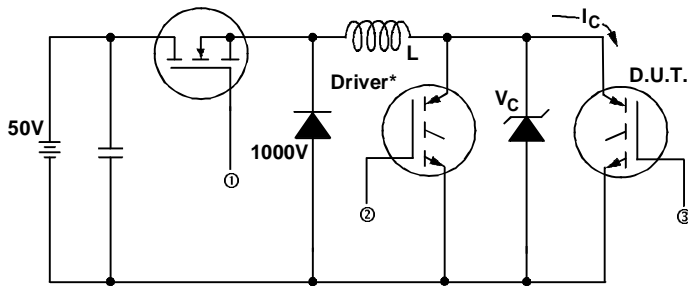


\* Driver same type as D.U.T.;  $V_c = 80\%$  of  $V_{ce(max)}$   
 \* Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated  $I_d$ .

**Fig. 13a** - Clamped Inductive Load Test Circuit

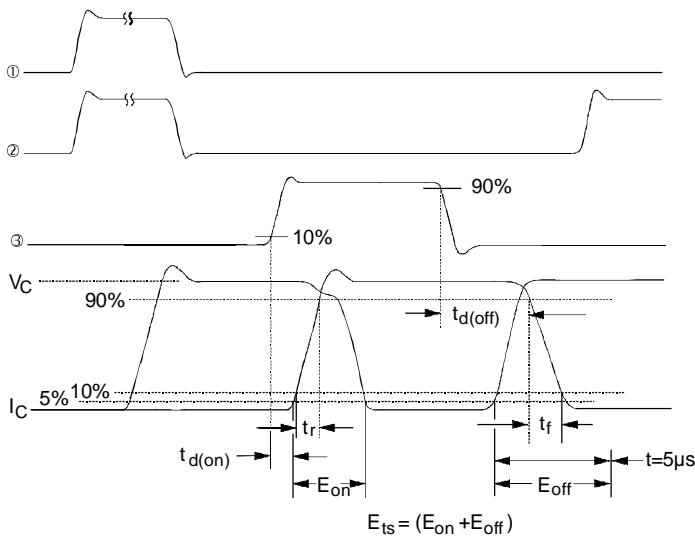


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_C = 480V$



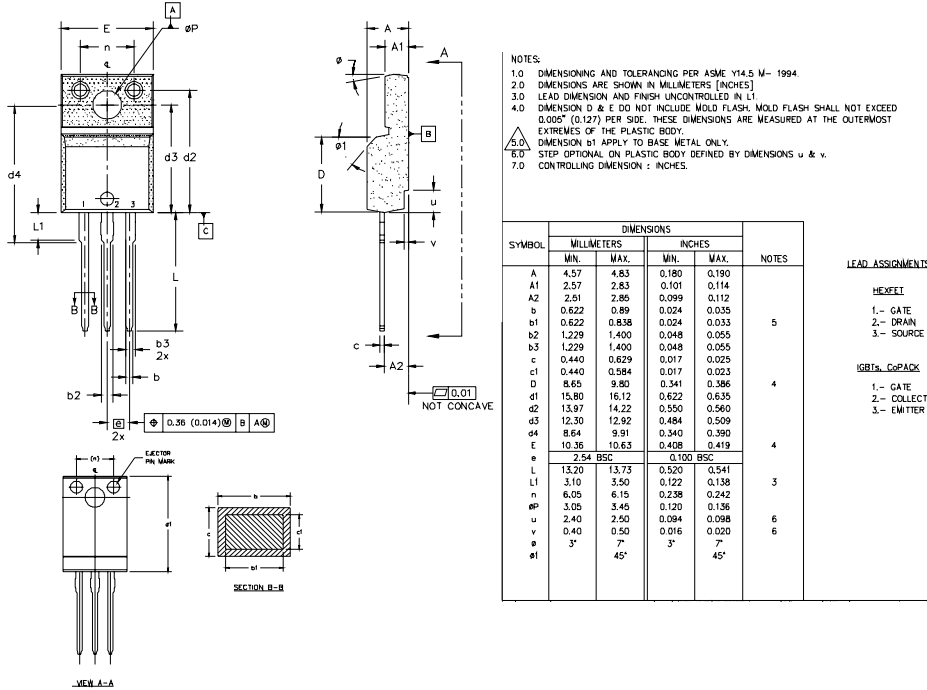
**Fig. 14b** - Switching Loss Waveforms

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International  
**IR** Rectifier

## TO-220 Full-Pak Package Outline

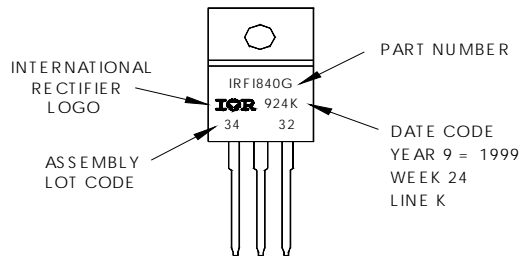
Dimensions are shown in millimeters (inches)



## TO-220 Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRF1840G  
WITH ASSEMBLY  
LOT CODE 3432  
ASSEMBLED ON WW 24 1999  
IN THE ASSEMBLY LINE "K"

**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.  
This product has been designed and qualified for the Industrial market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>